October 2008



FJA4310 NPN Epitaxial Silicon Transistor

- Audio Power Amplifier
- High Current Capability : I_C=10A
- High Power Dissipation
- Wide S.O.A
- Complement to FJA4210



Absolute Maximum Ratings* T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CBO}	Collector-Base Voltage	200	V	
V _{CEO}	Collector-Emitter Voltage	140	V	
V _{EBO}	Emitter-Base Voltage	6	V	
IC	Collector Current (DC)	10	A	
IB	Base Current (DC)	1.5	A	
P _C	Collector Dissipation (T _C =25°C)	100	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 ~ 150	°C	

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics* T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =5mA, I _E =0	200			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =50mA, R _{BE} =∞	140			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =5mA, I _C =0	6			V
I _{CBO}	Collector Cut-off Current	V _{CB} =200V, I _E =0			10	μA
I _{EBO}	Emitter Cut-off Current	V _{EB} =6V, I _C =0			10	μA
h _{FE}	* DC Current Gain	V _{CE} =4V, I _C =3A	50		180	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =5A, I _B =0.5A			0.5	V
C _{ob}	Output Capacitance	V _{CB} =10V, f=1MHz		250		pF
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =1A		30		MHz

* Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%

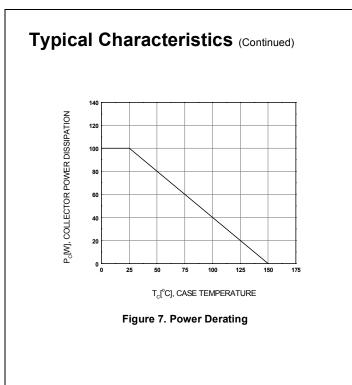
h_{FE} Classification

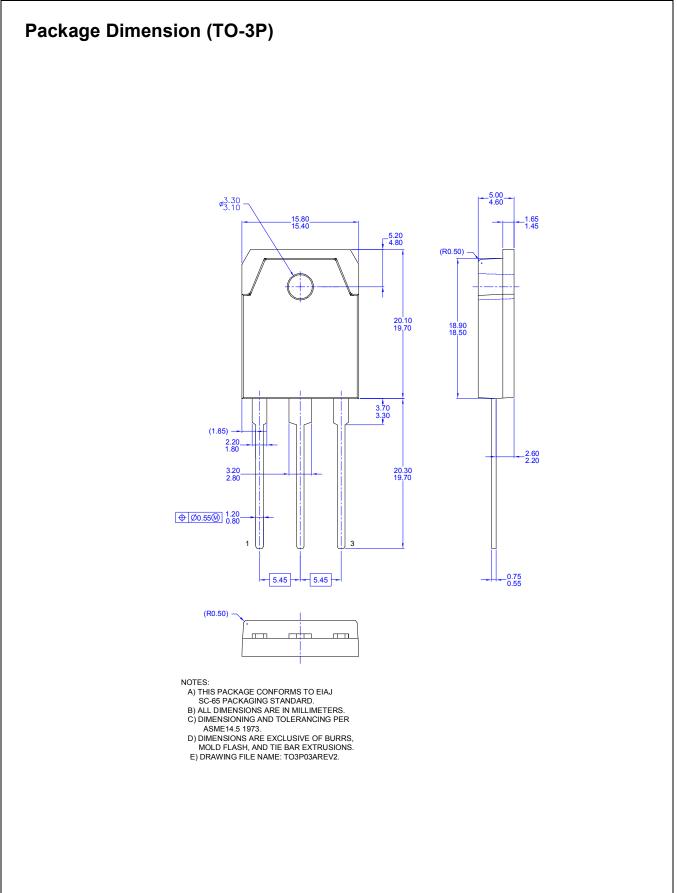
Classification	R	0	Y
h _{FE}	50 ~ 100	70 ~ 140	90 ~ 180

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Typical Characteristics 250mA 1000 I_B = 400m/ = 200mA V_CE = 4 V 150mA Ic [A], COLLECTOR CURRENT heed DC CURRENT GAIN I_B = 100mA Ta = 25 °C Ta = 125 °C 5 $I_{B} = 50 \text{mA}$ Ta = - 25 °C 2 I_B = 20mA 10 0.1 10 2 3 $\rm I_{\rm c}$ [A], COLLECTOR CURRENT V_{CE} [V], COLLECTOR-EMITTER VOLTAGE Figure 1. Static Characterstic Figure 2. DC current Gain 3. I_ = 10 I_ V_{cE}(sat) [V], SATURATION VOLTAGE $V_{CE}(sat)$ [V], SATURATION VOLTAGE 2.5 2.0 1.5 0.1 Ta = 25 1.0 - 25 °C Та 0.5 17= 10A - 5A 0.01 └─ 0.01 0.0 0.4 1.2 1.6 2.0 0.8 0.1 I_c [A], COLLECTOR CURRENT I_B [A], BASE CURRENT Figure 3. V_{CE}(sat) vs. I_B Characteristics Figure 4. Collector-Emitter Saturation Voltage V_{CE} = 4 V t=10ms I_ (Pulse) I_c [A], COLLECTOR CURRENT Ic [A], COLLECTOR CURRENT I (DC t=100 Ta = 25 °C 2 Ta = 125 T_c = 25°C Single Pulse 25 °C 0.1 0.0 10 100 0.5 1.0 1.5 V_{CE} [V], COLLECTOR-EMITTER VOLTAGE V_{BE} [V], Base-Emitter On VOLTAGE Figure 6. Forward Bias Safe Operating Area Figure 5. Base-Emitter On Voltage

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